

MM54HC4075/MM74HC4075 Triple 3-Input OR Gate

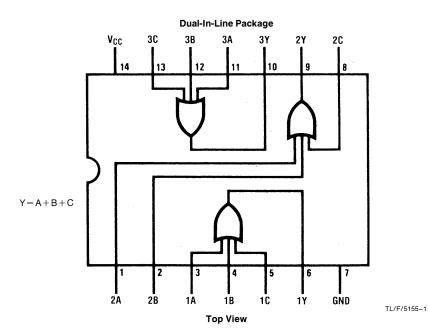
General Description

These OR gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs, providing high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pinout compatible with the standard 54LS/74LS logic family. The 54HC4075/74HC4075 is functionally equivalent and pin-out compatible with the CD4075B and MC14075B metal gate CMOS devices. All inputs are protected from damage due to static discharge by internal diode clamps to $\rm V_{CC}$ and ground.

Features

- Typical propagation delay: 11 ns
- Wide power supply range: 2V-6V
- Low quiescent current: 20 µA maximum (74HC Series)
- Low input current: 1 µA maximum
- Fanout of 10 LS-TTL loads

Connection Diagram



Order Number MM54HC4075 or MM74HC4075

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5 to $+7.0$ V
DC Input Voltage (V _{IN})	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V _{OUT})	-0.5 to $V_{\hbox{\footnotesize CC}}$ $+$ 0.5 $\hbox{\footnotesize V}$
Clamp Diode Current (I _{IK} , I _{OK})	\pm 20 mA
DC Output Current, per pin (IOUT)	\pm 25 mA
DC V _{CC} or GND Current, per pin (I _{CC})	\pm 50 mA
Storage Temperature Range (T _{STG})	-65°C to +150°C
Dawer Dissipation (D.)	

Power Dissipation (P_D)

600 mW (Note 3) S.O. Package only 500 mW 260°C

Lead Temp. (T_L) (Soldering 10 seconds)

Operating Condition	ons		
	Min	Max	Units
Supply Voltage (V _{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (TA)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times			
$(t_r, t_f) V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units	
				Тур		Guaranteed Limits]	
V_{IH}	Minimum High Level		2.0V		1.5	1.5	1.5	V	
	Input Voltage		4.5V 6.0V		3.15 4.2	3.15 4.2	3.15 4.2	V V	
V _{IL}	Maximum Low Level		2.0V		0.5	0.5	0.5	V	
	Input Voltage**		4.5V 6.0V		1.35 1.8	1.35 1.8	1.35 1.8	V V	
V _{OH}	Minimum High Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	v	
Output Voltage	Output voltage	IOUT \(\sum \) μΑ	4.5V 6.0V	4.5 6.0	4.4 5.9	4.4 5.9	4.4 5.9	V V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V V	
V _{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V V	
I _{IN}	Maximum Input Current	V _{IN} =V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μΑ	
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	μΑ	

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V $\pm 10\%$ the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

^{**}V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $v_{CC}\!=\!5\text{V},\,T_{A}\!=\!25^{\circ}\text{C},\,C_{L}\!=\!15\,\text{pF},\,t_{r}\!=\!t_{f}\!=\!6\,\text{ns}$

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay		11	20	ns

$\textbf{AC Electrical Characteristics} \ \ V_{CC} = 2.0 \ V \ \text{to 6.0V, C}_L = 50 \ \text{pF, t}_r = t_f = 6 \ \text{ns (unless otherwise specified)}$

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Propagation Delay		2.0V 4.5V 6.0V	40 12 10	115 23 20	145 29 25	171 34 29	ns ns ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	30 10 9	75 15 13	95 19 16	110 22 19	ns ns ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		30				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF

 $\textbf{Note 5:} \ \ C_{PD} \ \ \text{determines the no load dynamic power consumption, } \ P_D = C_{PD} \ \ V_{CC}^2 \ f + I_{CC} \ \ V_{CC}, \ \ \text{and the no load dynamic current consumption, } \ I_S = C_{PD} \ \ V_{CC} \ f + I_{CC}.$

Physical Dimensions inches (millimeters) 0.785 (19.939) MAX [14] [13] [12] [11] [10] [9] [8] 0.025 (0.635) RAD 0.220-0.310 (5.588-7.874) 1 2 3 4 5 6 7 0.290-0.320 0.005 0.200 (D.127) MIN (5.080) MAX 0.020-0.060 (7.366-8.128) GLASS 0.060 ±0.005 (1.524 ±0.127) 0.180 (0.508 - 1.524)MA 0.008-0.012 10° MAX (0.203-0.305) 0.310-0.410 D.018 ±0.003 0.125-0.200 0.098 (7.874 - 10.41)(0.457 ±0,076) (3.175-5.080) (2.489) MAX BOTH ENDS 0.100 ±0.010 0.150 (3.81) J14A (REV G) MIN Order Number MM54HC4075J or MM74HC4075J NS Package J14A AREA 1 2 3 4 5 6 7 0.092 DIA 0.030 MAX (0.762) DEPTH OPTION 1 OPTION 02 (1.651) 0.125 - 0.150 (3.175 - 3.810) 0.075 ±0.015 (1.905 ±0.381) 0.280 (7.112) MIN 0.014 - 0.023 (0.356 - 0.584) TYP 0.050 ± 0.010 (1.270 - 0.254) TYP (8.255 +1.016 -0.381 Order Number MM74HC4075N

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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